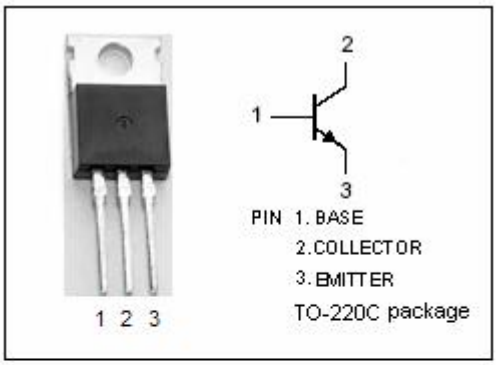
isc Silicon NPN Power Transistors 2N6773



DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = 400V(Min)
- High Switching Speed
- Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

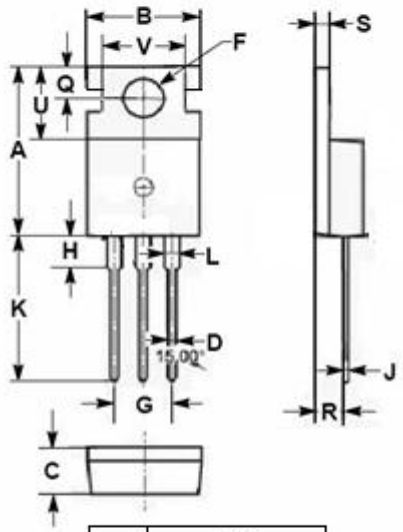
- Designed for use in off-line power supplies and is also well suited for use in a wide range of inverter or converter circuits and pulse-width-modulated regulators and switching applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	650	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	1	A
I_{CM}	Collector Current-Peak	3	A
P_C	Collector Power Dissipation@T_C=25℃	40	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	3.125	℃/W



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

isc Silicon NPN Power Transistors 2N6773

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA ; I_B= 0	400			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= 1mA ; I_C= 0	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= 1A; I_B= 0.2A I_C= 1A; I_B= 0.2A,T_C= 125℃			1.0 2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 1A; I_B= 0.2A			1.6	V
$V_{BE(on)}$	Base-Emitter On Voltage	I_C= 1A ; V_{CE}= 3V			1.5	V
I_{EBO}	Emitter Cutoff Current	V_{EB}= 6V; I_C=0			100	μA
I_{CBO}	Collector Cutoff Current	V_{CB}= 650V ; I_E= 0			100	μA
h_{FE}	DC Current Gain	I_C= 1A ; V_{CE}= 3V	10		50	
C_{OB}	Output Capacitance	I_E= 0;V_{CB}= 10V; f_{test}=1MHz	50			pF
f_T	Current-Gain—Bandwidth Product	I_C= 0.5A ;V_{CE}= 10V	10			MHz
Switching Times						
t_d	Delay Time	I_C= 1A; I_{B1}= -I_{B2}= 0.2A			0.1	μs
t_r	Rise Time				0.5	μs
t_{stg}	Storage Time				2.5	μs
t_f	Fall Time				0.4	μs

isc Silicon NPN Power Transistors 2N6773

NOTICE：
ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.
ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.
ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.